

TLP251

INVERTER FOR AIR CONDITIONOR
 INDUCTION HEATING
 TRANSISTOR INVERTER
 POWER MOS FET GATE DRIVE
 IGBT GATE DRIVE

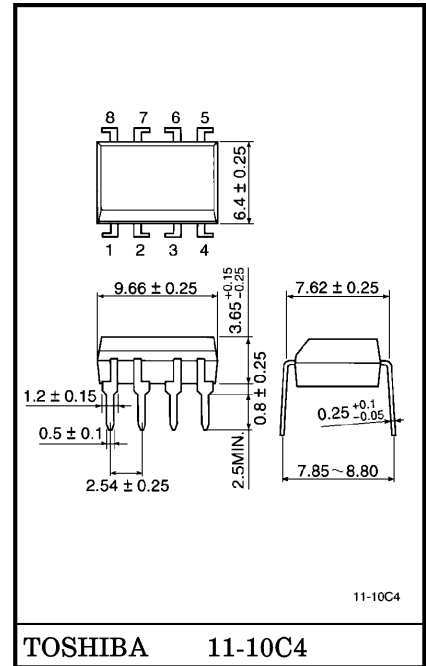
The TOSHIBA TLP251 consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP package.

TLP251 is suitable for gate driving circuit of IGBT or power MOS FET. Especially TLP251 is capable of "direct" gate drive of lower power IGBTs. (~15A)

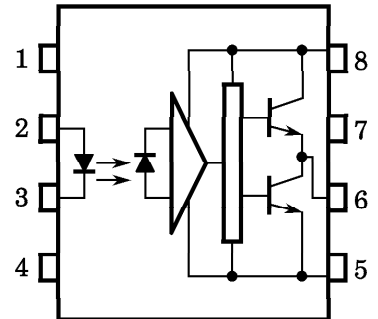
- Input Threshold Current : $I_F = 5\text{mA}$ (Max.)
- Supply Current (I_{CC}) : 11mA (Max.)
- Supply Voltage (V_{CC}) : 10-35V
- Output Current (I_O) : $\pm 0.4\text{A}$ (Max.)
- Switching Time (t_{pLH}/t_{pHL}) : $1\mu\text{s}$ (Max.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

Unit in mm



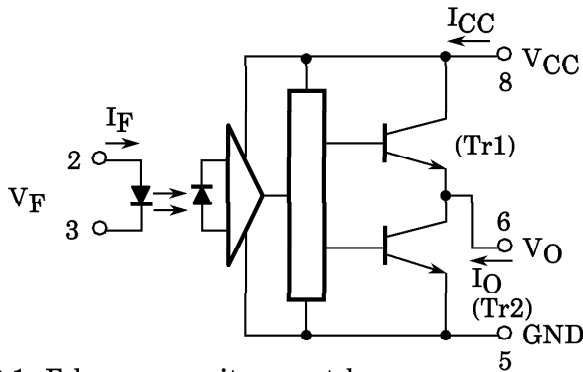
Weight : 0.54g

PIN CONFIGURATION (TOP VIEW)



- 1 : N.C.
- 2 : ANODE
- 3 : CATHODE
- 4 : N.C.
- 5 : GND
- 6 : V_O (OUTPUT)
- 7 : N.C.
- 8 : V_{CC}

SCHMATIC



A $0.1\mu\text{F}$ bypass capacitor must be connected between pin 8 and 5 (See Note 5).

TRUTH TABLE

		Tr1	Tr2
Input LED	ON	ON	OFF
	OFF	OFF	ON

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
LED	Forward Current	I_F	20	mA	
	Forward Current Derating (Ta ≥ 70°C)	$\Delta I_F / \Delta Ta$	-0.36	mA / °C	
	Peak Transient Forward Current (Note 1)	I_{FPT}	1	A	
	Reverse Voltage	V_R	5	V	
	Junction Temperature	T_j	125	°C	
DETECTOR	“H” Peak Output Current ($P_W \leq 2.0 \mu s$, $f \leq 15 \text{kHz}$) (Note 2)	I_{OPH}	-0.4	A	
	“L” Peak Output Current ($P_W \leq 2.0 \mu s$, $f \leq 15 \text{kHz}$) (Note 2)	I_{OPL}	0.4	A	
	Output Voltage	(Ta ≤ 70°C)	V_O	35	V
		(Ta = 85°C)		24	
	Supply Voltage	(Ta ≤ 70°C)	V_{CC}	35	V
		(Ta = 85°C)		24	
	Output Voltage Derating (Ta ≥ 70°C)	$\Delta V_O / \Delta Ta$	-0.73	V / °C	
	Supply Voltage Derating (Ta ≥ 70°C)	$\Delta V_{CC} / \Delta Ta$	-0.73	V / °C	
Junction Temperature	T_j	125	°C		
Operating Frequency (Note 3)	f	25	kHz		
Operating Temperature Range	T_{opr}	-20~85	°C		
Storage Temperature Range	T_{stg}	-55~125	°C		
Lead Soldering Temperature (10s)	T_{sol}	260	°C		
Isolation Voltage (AC, 1min., R.H. ≤ 60%) (Note 4)	BV_S	2500	Vrms		

(Note 1) Pulse width $P_W \leq 1 \mu s$, 300pps

(Note 2) Exponential Waveform

(Note 3) Exponential Waveform, $I_{OPH} \leq -0.25A (\leq 2.0 \mu s)$, $I_{OPL} \leq +0.25A (\leq 2.0 \mu s)$

(Note 4) Device considered a two terminal device : pins 1,2,3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

(Note 5) A ceramic capacitor (0.1 μ F) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1cm.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input Current, ON	I_F (ON)	7	8	10	mA
Input Voltage, OFF	V_F (OFF)	0	—	0.8	V
Supply Voltage	V_{CC}	10	—	30 20	V
Peak Output Current	I_{OPH}/I_{OPL}	—	—	± 0.1	A
Operating Temperature	T_{opr}	-20	25	70 85	°C

ELECTRICAL CHARACTERISTICS ($T_a = -20 \sim 70^\circ\text{C}$, Unless otherwise specified)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.*	MAX.	UNIT		
Input Forward Voltage	V_F	—	$I_F = 10\text{mA}$, $T_a = 25^\circ\text{C}$	—	1.6	1.8	V		
Temperature Coefficient of Forward Voltage	$\Delta V_F / \Delta T_a$	—	$I_F = 10\text{mA}$	—	-2.0	—	mV / °C		
Input Reverse Current	I_R	—	$V_R = 5\text{V}$, $T_a = 25^\circ\text{C}$	—	—	10	μA		
Input Capacitance	C_T	—	$V = 0$, $f = 1\text{MHz}$, $T_a = 25^\circ\text{C}$	—	45	250	pF		
Output Current	“H” Level	I_{OPH}	3	$V_{CC} = 30\text{V}$ (*1)	$I_F = 10\text{mA}$ $V_{8-6} = 4\text{V}$	-0.1	-0.25	—	A
	“L” Level	I_{OPL}	2			$I_F = 0$ $V_{6-5} = 2.5\text{V}$	0.1	0.2	
Output Voltage	“H” Level	V_{OH}	4	$V_{CC1} = +15\text{V}$, $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$, $I_F = 5\text{mA}$		11	13.2	—	V
	“L” Level	V_{OL}	5	$V_{CC1} = +15\text{V}$, $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$, $V_F = 0.8\text{V}$		—	-14.5	-12.5	
Supply Current	“H” Level	I_{CCH}	—	$V_{CC} = 30\text{V}$, $I_F = 10\text{mA}$ $T_a = 25^\circ\text{C}$		—	7.5	—	mA
				$V_{CC} = 30\text{V}$, $I_F = 10\text{mA}$		—	—	11	
	“L” Level	I_{CCL}	—	$V_{CC} = 30\text{V}$, $I_F = 0\text{mA}$ $T_a = 25^\circ\text{C}$		—	8	—	
				$V_{CC} = 30\text{V}$, $I_F = 0\text{mA}$		—	—	11	
Threshold Input Current	“Output L→H”	I_{FLH}	—	$V_{CC1} = +15\text{V}$, $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$, $V_O > 0\text{V}$		—	1.2	5	mA
Threshold Input Voltage	“Output H→L”	V_{FHL}	—	$V_{CC1} = +15\text{V}$, $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$, $V_O < 0\text{V}$		0.8	—	—	V
Supply Voltage	V_{CC}	—				10	—	35	V
Capacitance (Input-Output)	C_s	—		$V_s = 0$, $f = 1\text{MHz}$ $T_a = 25^\circ\text{C}$		—	1.0	2.0	pF
Resistance (Input-Output)	R_s	—		$V_s = 500\text{V}$, $T_a = 25^\circ\text{C}$ $R.H. \leq 60\%$		1×10^{12}	10^{14}	—	Ω

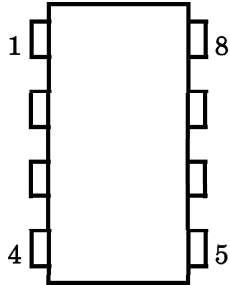
* All typical values are at $T_a = 25^\circ\text{C}$ (*1) : Duration of I_O time $\leq 50\mu\text{s}$

SWITCHING CHARACTERISTICS (Ta = -20~70°C, Unless otherwise specified)

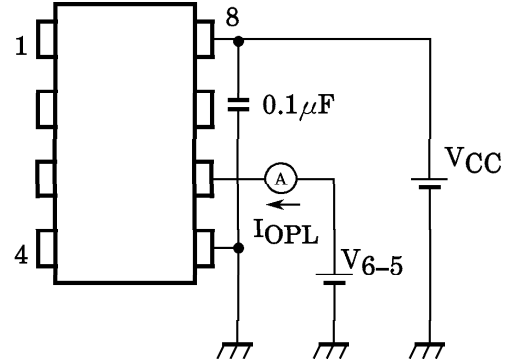
CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.*	MAX.	UNIT
Propagation Delay Time	L→H	t _{pLH}	6	I _F = 8mA V _{CC1} = +15V, V _{EE1} = -15V R _L = 200Ω	—	0.25	1.0	μs
	H→L	t _{pHL}			—	0.25	1.0	
Output Rise Time		t _r			—	—	—	
Output Fall Time		t _f			—	—	—	
Common Mode Transient Immunity at High Level Output		C _{MH}	7	V _{CM} = 600V, I _F = 8mA V _{CC} = 30V, Ta = 25°C	-5000	—	—	V / μs
Common Mode Transient Immunity at Low Level Output		C _M L	7	V _{CM} = 600V, I _F = 0mA V _{CC} = 30V, Ta = 25°C	5000	—	—	V / μs

* All typical values are at Ta = 25°C

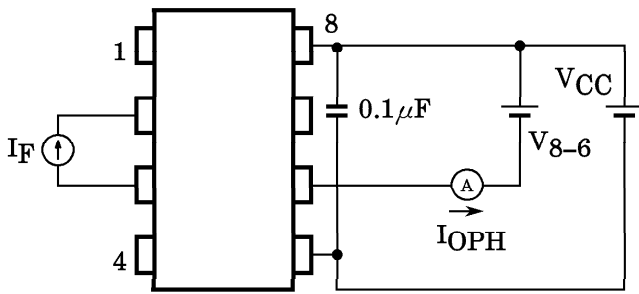
TEST CIRCUIT 1 :



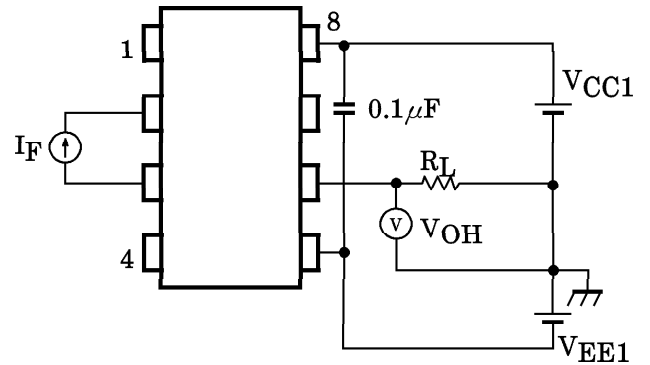
TEST CIRCUIT 2 : I_{OPL}



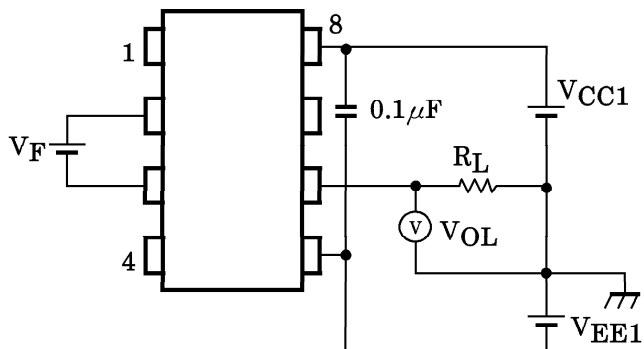
TEST CIRCUIT 3 : I_{OPH}



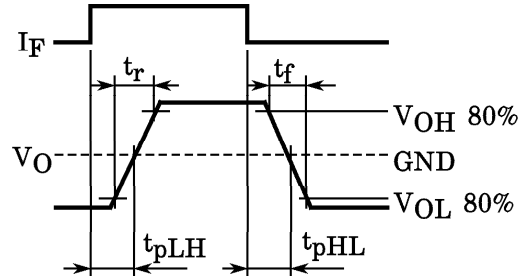
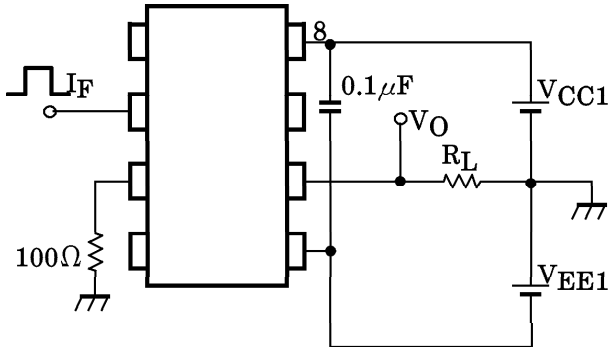
TEST CIRCUIT 4 : V_{OH}



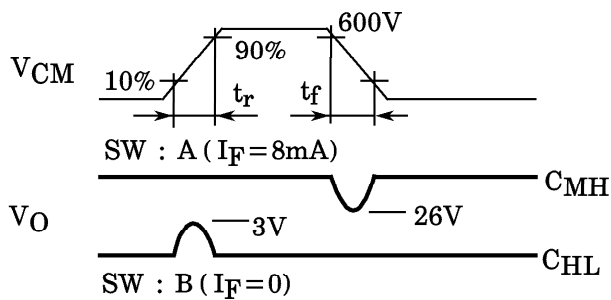
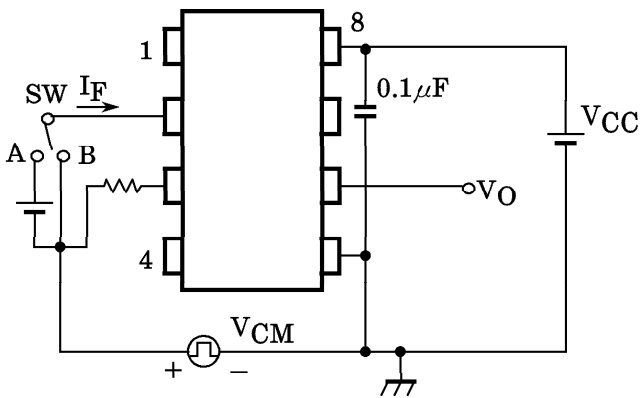
TEST CIRCUIT 5 : V_{OL}



TEST CIRCUIT 6 : t_{pLH} , t_{pHL} , t_r , t_f



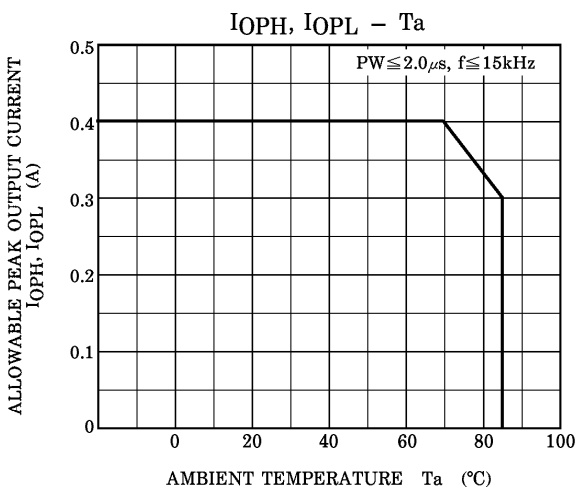
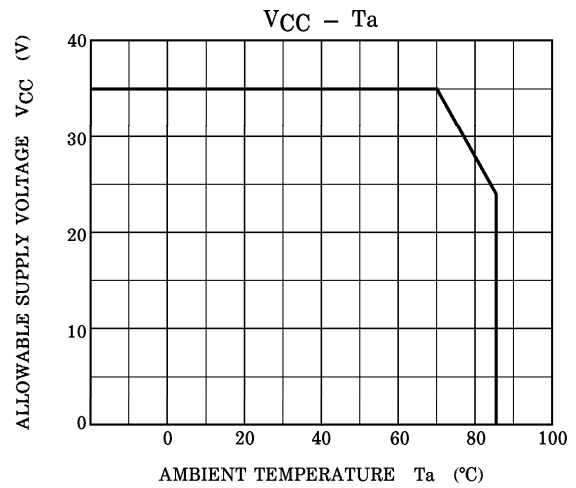
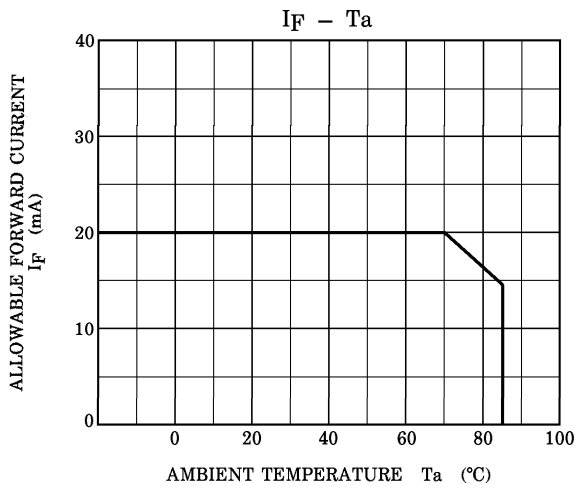
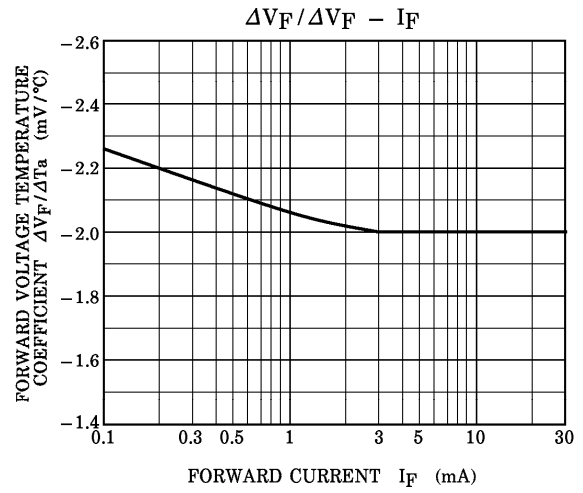
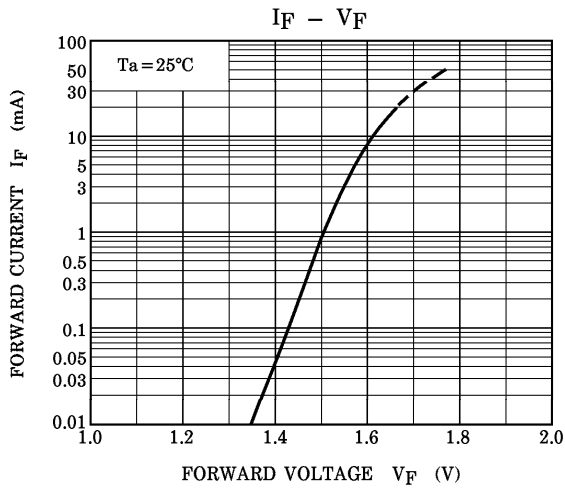
TEST CIRCUIT 7 : C_{MH} , C_{ML}



$$C_{ML} = \frac{480(V)}{t_r(\mu s)}$$

$$C_{MH} = \frac{480(V)}{t_f(\mu s)}$$

C_{ML} (C_{MH}) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.



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